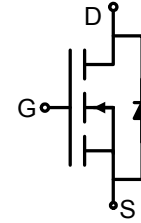




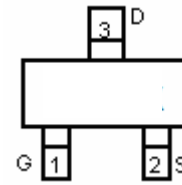
N-Channel Enhancement Mode Power MOSFET

Description

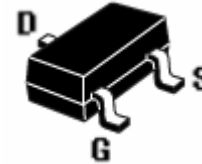
The IRLML2060 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a Battery protection or in other switching application.



Schematic Diagram



Marking and Pin Assignment



SOT-23 Top View

General Features

- $V_{DS} = 60V, I_D = 1.8A$
- $R_{DS(ON)}$ Typ=142m Ω @ $V_{GS}=10V$
- $R_{DS(ON)}$ Typ=165m Ω @ $V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- DC/DC converter

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A8***	IRLML2060	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	1.8	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	8	A
Maximum Power Dissipation	P_D	1.6	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	78	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA



Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2A$	-	142	185	m Ω
		$V_{GS}=4.5V, I_D=2A$	-	165	230	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=2A$	-	3	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ d $F=1.0MHz$	-	384	-	PF
Output Capacitance	C_{oss}		-	25	-	PF
Reverse Transfer Capacitance	C_{rss}		-	20	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A$ $V_{GS}=10V, R_{GEN}=1\Omega$	-	8	-	nS
Turn-on Rise Time	t_r		-	6	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	12	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=2A,$ $V_{GS}=10V$	-	11.9	-	nC
Gate-Source Charge	Q_{gs}		-	2.0	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=2A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	2	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

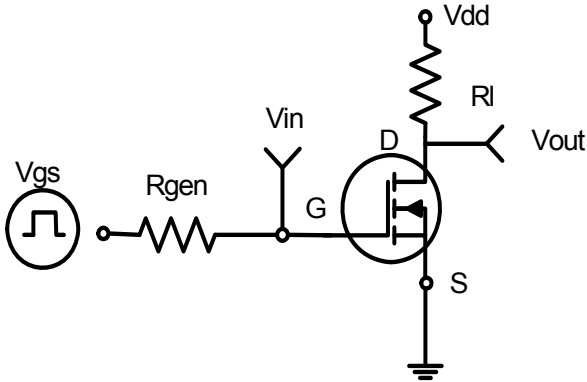


Figure 1: Switching Test Circuit

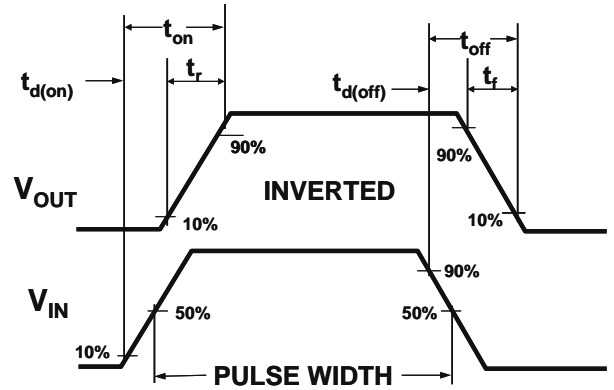


Figure 2: Switching Waveforms

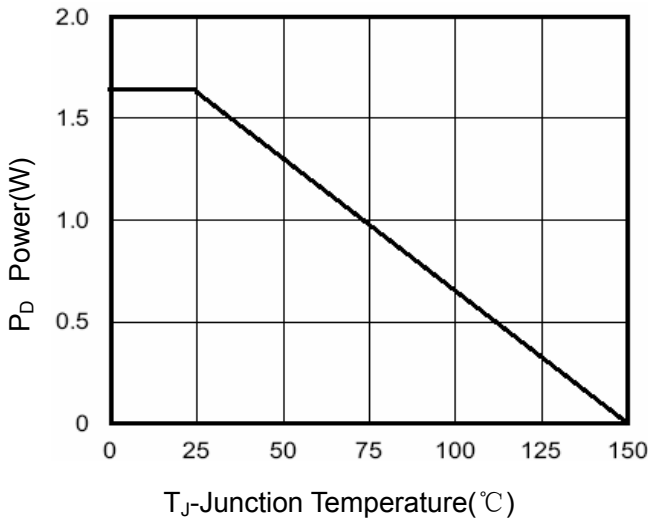


Figure 3 Power Dissipation

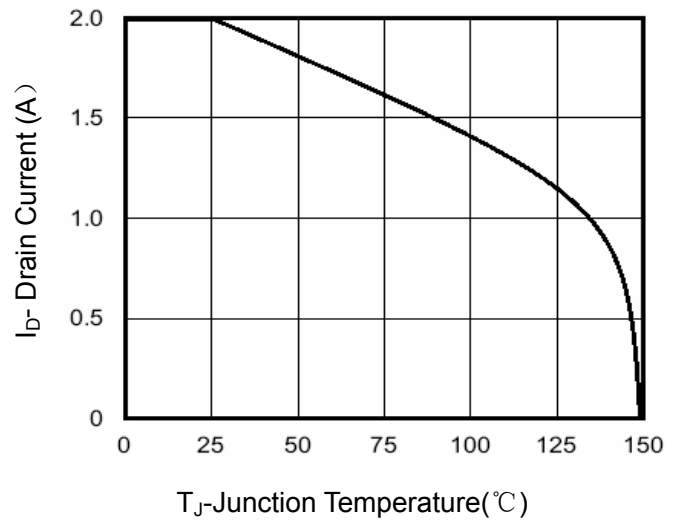


Figure 4 Drain Current

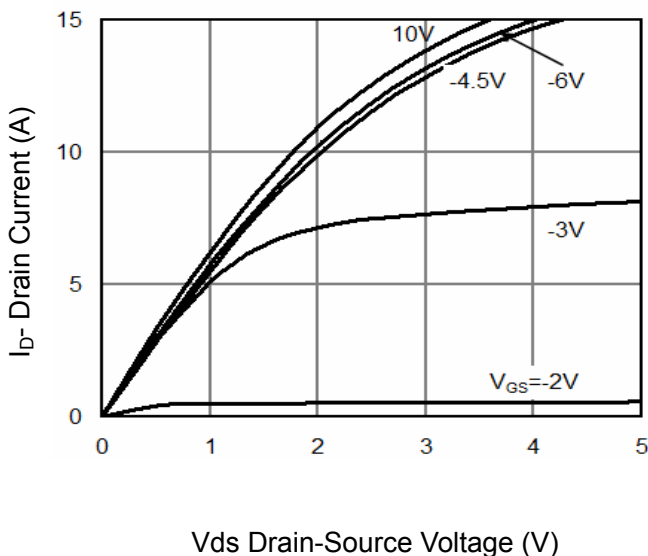


Figure 5 Output Characteristics

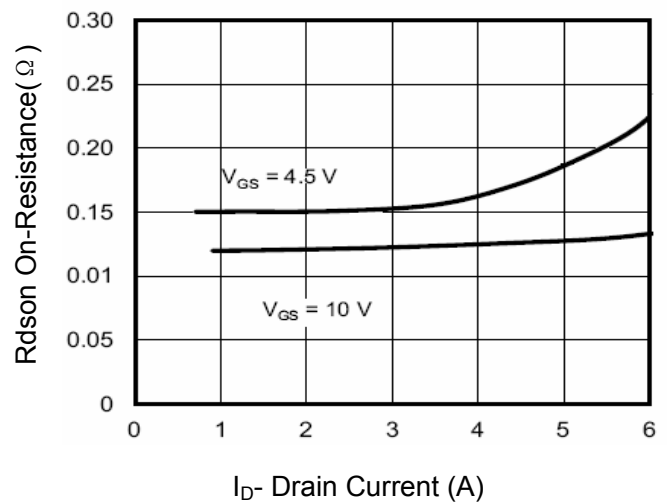


Figure 6 Drain-Source On-Resistance

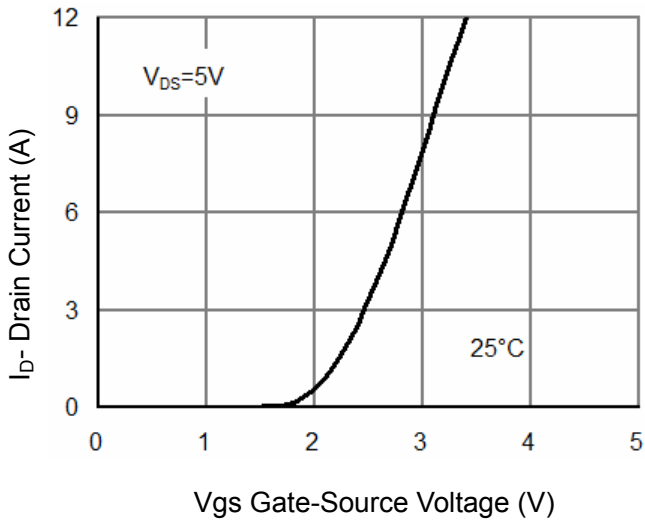


Figure 7 Transfer Characteristics

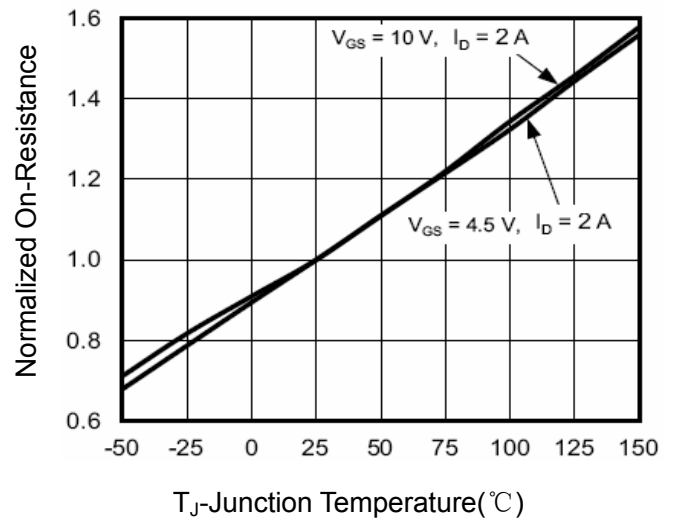


Figure 8 Drain-Source On-Resistance

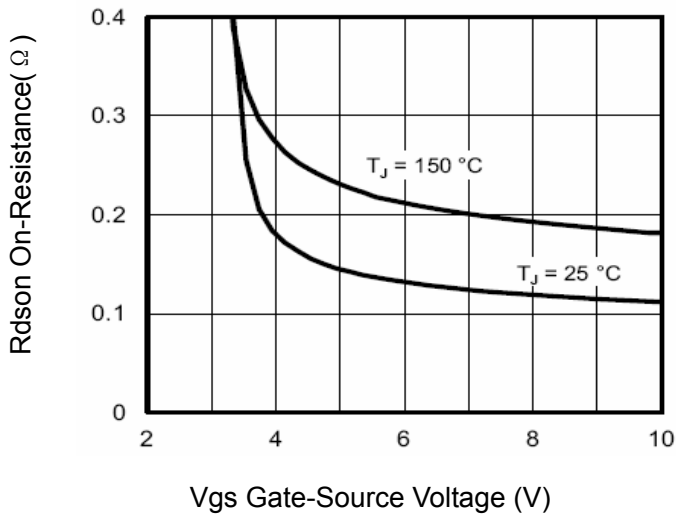


Figure 9 Rdson vs Vgs

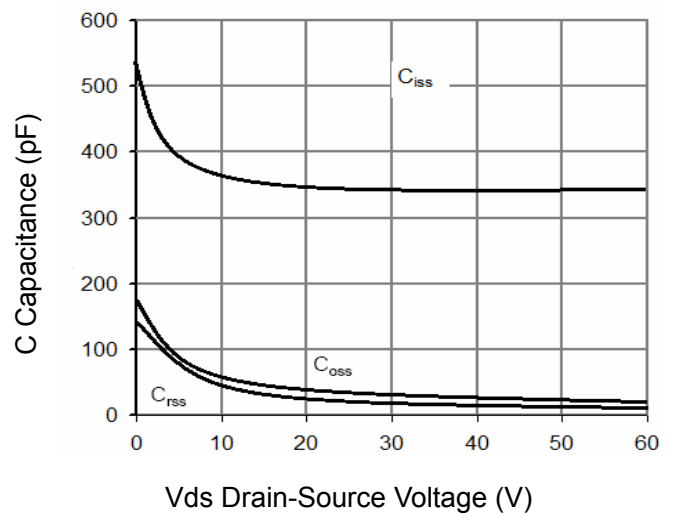


Figure 10 Capacitance vs Vds

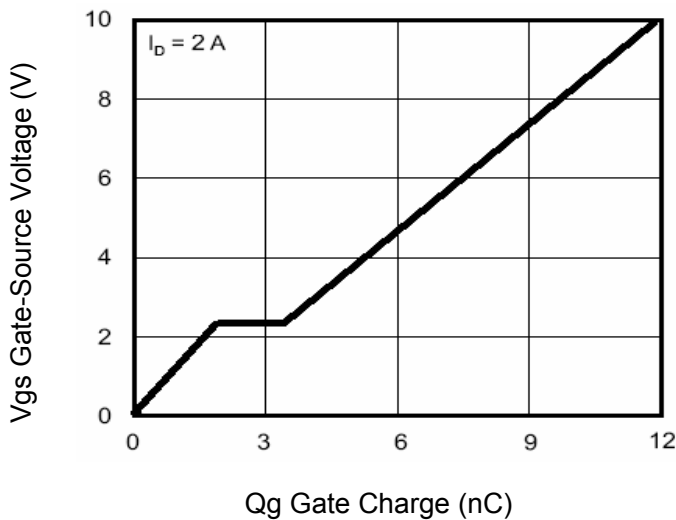


Figure 11 Gate Charge

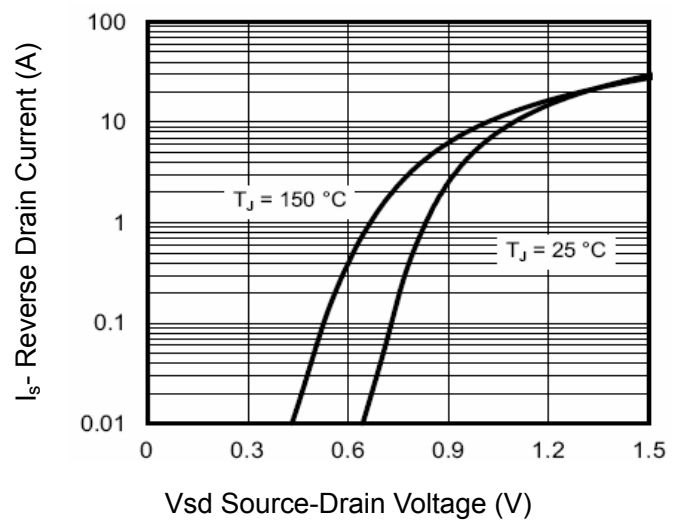


Figure 12 Source-Drain Diode Forward

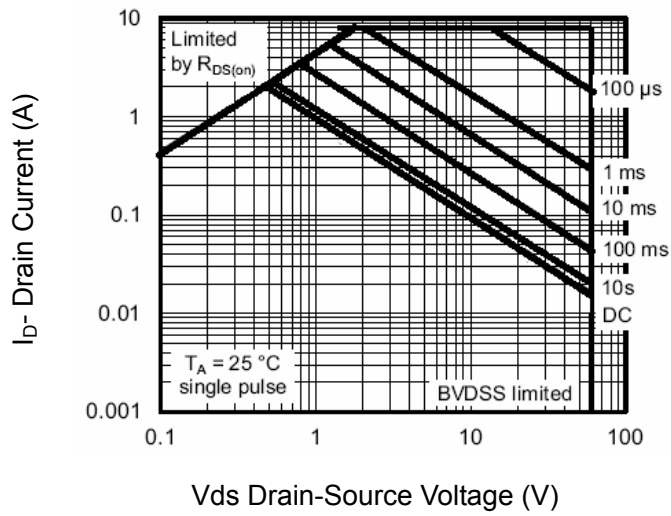


Figure 13 Safe Operation Area

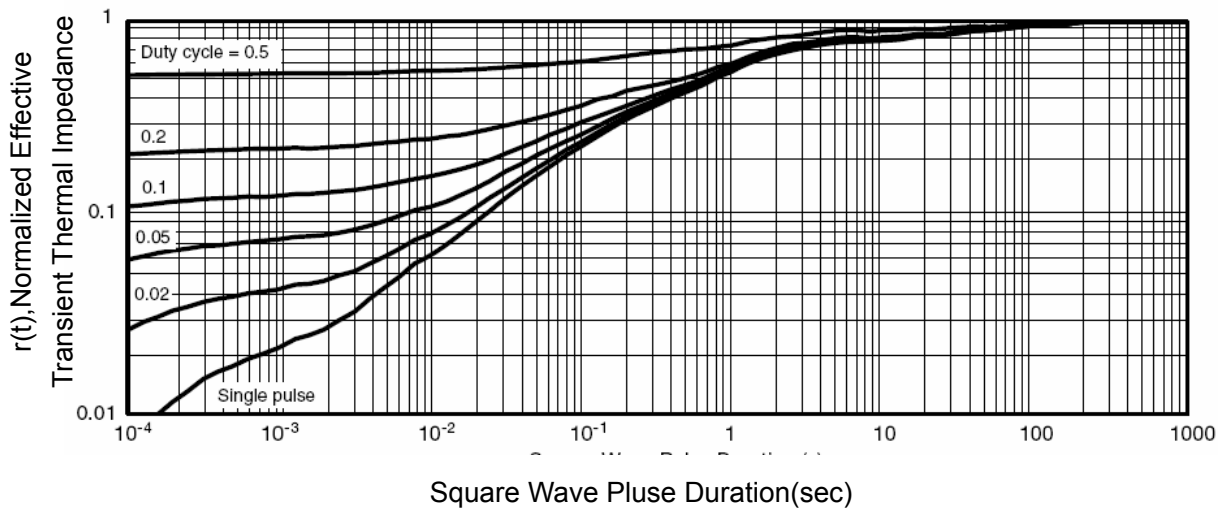
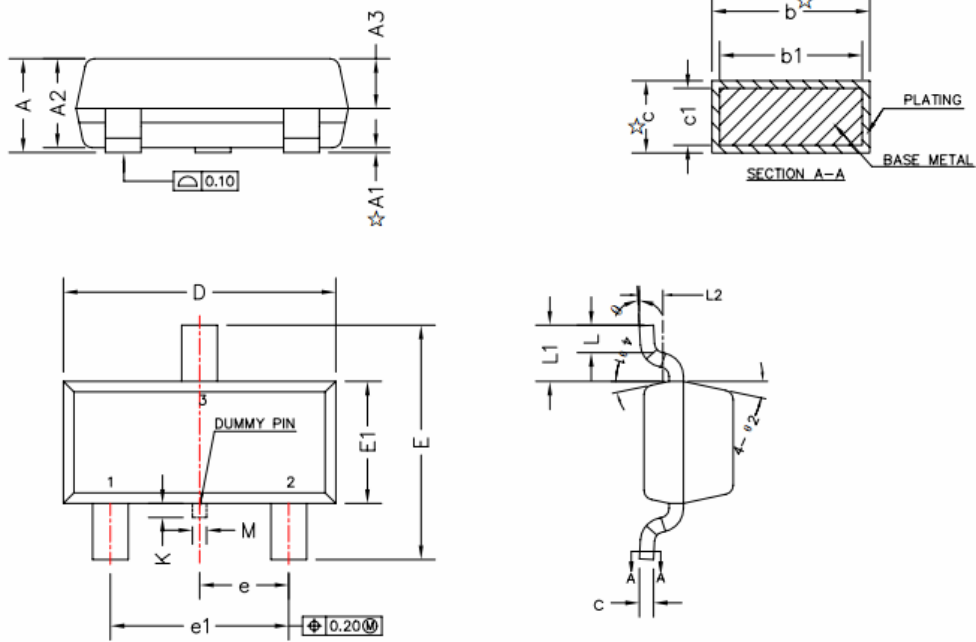


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Millimeters	
	Min.	Max.
A	0.89	1.12
A1	0.01	0.10
A2	0.88	1.02
A3	0.43	0.63
b	0.36	0.50
b1	0.35	0.45
c	0.14	0.20
c1	0.14	0.16
D	2.80	3.00
E	2.35	2.64
E1	1.20	1.40
e	0.90	1.00
e1	1.80	2.00
L	0.40	0.60
L1	0.6REF	
L2	0.25BSC	
M	0.10	0.25
K	0.00	0.25
θ	0°	8°
θ_1	10°	14°
θ_2	10°	14°